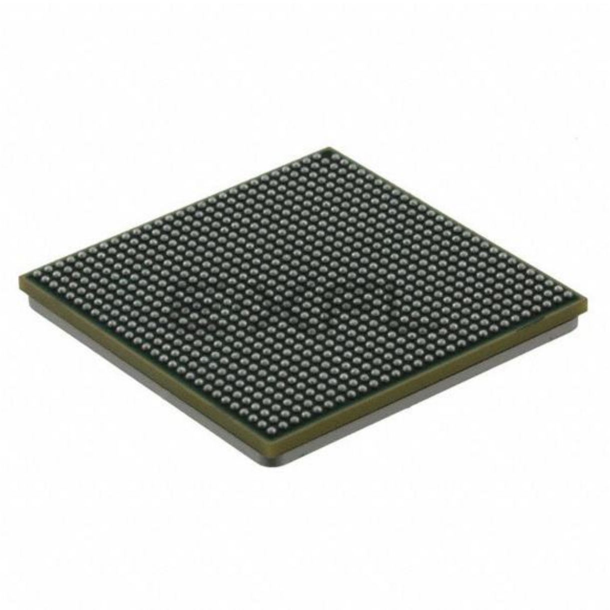

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.2GHz
Co-Processors/DSP	Signal Processing; SPE
RAM Controllers	DDR, DDR2, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8548vtatgc

NOTE

From a system standpoint, if any of the I/O power supplies ramp prior to the V_{DD} core supply, the I/Os associated with that I/O supply may drive a logic one or zero during power-up, and extra current may be drawn by the device.

3 Power Characteristics

The estimated typical power dissipation for the core complex bus (CCB) versus the core frequency for this family of PowerQUICC III devices is shown in the following table.

Table 4. Device Power Dissipation

CCB Frequency[1]	Core Frequency	SLEEP[2]	Typical-65[3]	Typical-105[4]	Maximum[5]	Unit
400	800	2.7	4.6	7.5	8.1	W
	1000	2.7	5.0	7.9	8.5	W
	1200	2.7	5.4	8.3	8.9	
500	1500	11.5	13.6	16.5	18.6	W
533	1333	6.2	7.9	10.8	12.8	W

Notes:

1. CCB frequency is the SoC platform frequency, which corresponds to the DDR data rate.
2. SLEEP is based on V_{DD} = 1.1 V, T_j = 65°C.
3. Typical-65 is based on V_{DD} = 1.1 V, T_j = 65°C, running Dhrystone.
4. Typical-105 is based on V_{DD} = 1.1 V, T_j = 105°C, running Dhrystone.
5. Maximum is based on V_{DD} = 1.1 V, T_j = 105°C, running a smoke test.

6 DDR and DDR2 SDRAM

This section describes the DC and AC electrical specifications for the DDR SDRAM interface of the device. Note that GV_{DD}(typ) = 2.5 V for DDR SDRAM, and GV_{DD}(typ) = 1.8 V for DDR2 SDRAM.

6.1 DDR SDRAM DC Electrical Characteristics

The following table provides the recommended operating conditions for the DDR2 SDRAM controller of the device when GV_{DD}(typ) = 1.8 V.

Table 11. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	1.71	1.89	V	1
I/O reference voltage	MV_{REF}	0.49 × GV_{DD}	0.51 × GV_{DD}	V	2
I/O termination voltage	V_{TT}	MV_{REF} – 0.04	MV_{REF} + 0.04	V	3
Input high voltage	V_{IH}	MV_{REF} + 0.125	GV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	MV_{REF} – 0.125	V	—
Output leakage current	I_{OZ}	–50	50	μA	4
Output high current (V_{OUT} = 1.420 V)	I_{OH}	–13.4	—	mA	—
Output low current (V_{OUT} = 0.280 V)	I_{OL}	13.4	—	mA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM V_{DD} at all times.
2. MV_{REF} is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail must track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.

This table provides the DDR2 I/O capacitance when GV_{DD}(typ) = 1.8 V.

Table 12. DDR2 SDRAM Capacitance for GV_{DD}(typ)=1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 1.8 V ± 0.090 V, f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

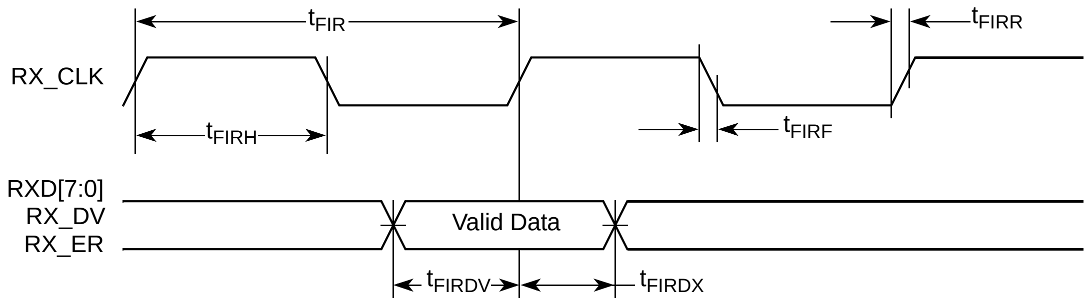


Figure 7. FIFO Receive AC Timing Diagram

8.2.2 GMII AC Timing Specifications

This section describes the GMII transmit and receive AC timing specifications.

8.2.2.1 GMII Transmit AC Timing Specifications

This table provides the GMII transmit AC timing specifications.

Table 26. GMII Transmit AC Timing Specifications

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
GMII data TXD[7:0], TX_ER, TX_EN setup time	t_{GTKHDV}	2.5	—	—	ns
GTX_CLK to GMII data TXD[7:0], TX_ER, TX_EN delay	t_{GTKHDX}	0.5	—	5.0	ns
GTX_CLK data clock rise time (20%–80%)	t_{GTXR}[2]	—	—	1.0	ns
GTX_CLK data clock fall time (80%–20%)	t_{GTXF}[2]	—	—	1.0	ns

Notes:

1. The symbols used for timing specifications follow the pattern $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{GTKHDV} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) reaching the valid state (V) to state or setup time. Also, t_{GTKHDX} symbolizes GMII transmit timing (GT) with respect to the t_{GTX} clock reference (K) going to the high state (H) relative to the time date input signals (D) going invalid (X) or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{GTX} represents the GMII(G) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. Guaranteed by design.

Table 37. MII Management AC Timing Specifications (continued)

At recommended operating conditions with OV_{DD} is 3.3 V ± 5%.

Parameter	Symbol[1]	Min	Typ	Max	Unit	Notes
MDC fall time	t_{MDHF}	—		10	ns	4

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MDKHDX} symbolizes management data timing (MD) for the time t_{MDC} from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, t_{MDDVKH} symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MDC} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. This parameter is dependent on the eTSEC system clock speed, which is half of the Platform Frequency (f_{CCB}). The actual ECn_MDC output clock frequency for a specific eTSEC port can be programmed by configuring the MgmtClk bit field of device's MIIMCFG register, based on the platform (CCB) clock running for the device. The formula is: Platform Frequency (CCB) ÷ (2 × Frequency Divider determined by MIICFG[MgmtClk] encoding selection). For example, if MIICFG[MgmtClk] = 000 and the platform (CCB) is currently running at 533 MHz, f_{MDC} = 533) ÷ (2 × 4 × 8) = 533) ÷ 64 = 8.3 MHz. That is, for a system running at a particular platform frequency (f_{CCB}), the ECn_MDC output clock frequency can be programmed between maximum $f_{MDC} = f_{CCB} \div 64$ and minimum $f_{MDC} = f_{CCB} \div 448$. See 14.5.3.6.6, "MII Management Configuration Register (MIIMCFG)," in the *MPC8548E PowerQUICC™ III Integrated Processor Family Reference Manual* for more detail.
3. The maximum ECn_MDC output clock frequency is defined based on the maximum platform frequency for device (533 MHz) divided by 64, while the minimum ECn_MDC output clock frequency is defined based on the minimum platform frequency for device (333 MHz) divided by 448, following the formula described in Note 2 above.
4. Guaranteed by design.
5. t_{CCB} is the platform (CCB) clock period.

Figure 21 shows the MII management AC timing diagram.

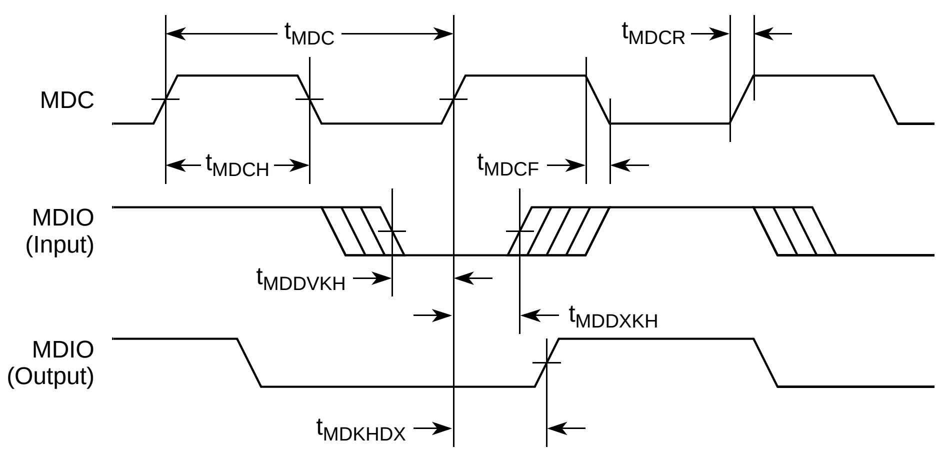


Figure 21. MII Management Interface Timing Diagram

NOTE

PLL bypass mode is required when LBIU frequency is at or below 83 MHz. When LBIU operates above 83 MHz, LBIU PLL is recommended to be enabled.

Figure 23 through Figure 28 show the local bus signals.

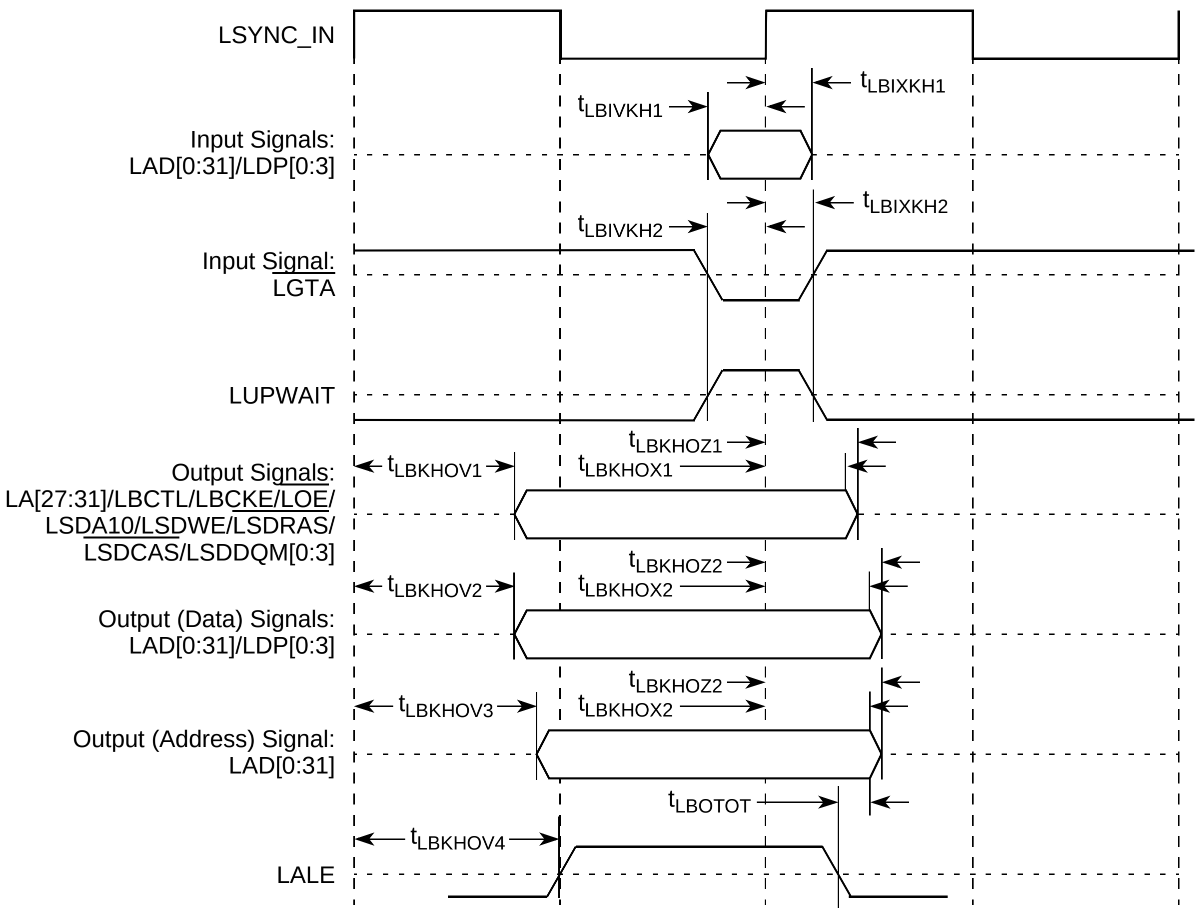


Figure 23. Local Bus Signals (PLL Enabled)

This table describes the timing parameters of the local bus interface at BV_{DD} = 3.3 V with PLL disabled.

Table 42. Local Bus Timing Parameters—PLL Bypassed

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	12	—	ns	2
Local bus duty cycle	t_{LBKH}/t_{LBK}	43	57	%	—
Internal launch/capture clock to LCLK delay	t_{LBKHKT}	2.3	4.4	ns	8
Input setup to local bus clock (except $\overline{\text{LGTA}}$/LUPWAIT)	$t_{LBIVKH1}$	6.2	—	ns	4, 5
$\overline{\text{LGTA}}$/LUPWAIT input setup to local bus clock	$t_{LBIVKL2}$	6.1	—	ns	4, 5
Input hold from local bus clock (except $\overline{\text{LGTA}}$/LUPWAIT)	$t_{LBIXKH1}$	–1.8	—	ns	4, 5

Table 46. I^2C AC Electrical Specifications (continued)

Parameter	Symbol[1]	Min	Max	Unit	Notes
Noise margin at the LOW level for each connected device (including hysteresis)	V_{NL}	$0.1 \times OV_{DD}$	—	V	—
Noise margin at the HIGH level for each connected device (including hysteresis)	V_{NH}	$0.2 \times OV_{DD}$	—	V	—

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{I2DVKH} symbolizes I^2C timing (I2) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. Also, t_{I2SXKL} symbolizes I^2C timing (I2) for the time that the data with respect to the start condition (S) went invalid (X) relative to the t_{I2C} clock reference (K) going to the low (L) state or hold time. Also, t_{I2PVKH} symbolizes I^2C timing (I2) for the time that the data with respect to the stop condition (P) reaching the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. As a transmitter, the device provides a delay time of at least 300 ns for the SDA signal (see the V_{IH}(min) of the SCL signal) to bridge the undefined region of the falling edge of SCL to avoid unintended generation of Start or Stop condition. When the device acts as the I^2C bus master while transmitting, the device drives both SCL and SDA. As long as the load on SCL and SDA are balanced, the device would not cause unintended generation of Start or Stop condition. Therefore, the 300 ns SDA output delay time is not a concern. If, under some rare condition, the 300 ns SDA output delay time is required for the device as a transmitter, the following setting is recommended for the FDR bit field of the I2CFDR register to ensure both the desired I^2C SCL clock frequency and SDA output delay time are achieved, assuming that the desired I^2C SCL clock frequency is 400 kHz and the Digital Filter Sampling Rate Register (I2CDFSRR) is programmed with its default setting of 0x10 (decimal 16):

I^2C source clock frequency	333 MHz	266 MHz	200 MHz	133 MHz
FDR bit setting	0x2A	0x05	0x26	0x00
Actual FDR divider selected	896	704	512	384
Actual I^2C SCL frequency generated	371 kHz	378 kHz	390 kHz	346 kHz

   For the detail of I^2C frequency calculation, see *Determining the I^2C Frequency Divider Ratio for SCL* (AN2919). Note that the I^2C source clock frequency is half of the CCB clock frequency for the device.
3. The maximum t_{I2DXKL} has only to be met if the device does not stretch the LOW period (t_{I2CL}) of the SCL signal.
4. Guaranteed by design.

Figure 33 provides the AC test load for the I^2C.

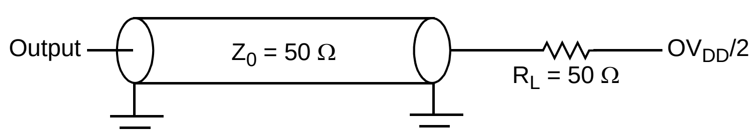


Figure 33. I^2C AC Test Load

Table 56. Differential Transmitter (TX) Output Specifications (continued)

Symbol	Parameter	Min	Nom	Max	Unit	Comments
$T_{crosslink}$	Crosslink random timeout	0	—	1	ms	This random timeout helps resolve conflicts in crosslink configuration by eventually resulting in only one downstream and one upstream port. See Note 7.

Notes:

1. No test load is necessarily associated with this value.
2. Specified at the measurement point into a timing and voltage compliance test load as shown in Figure 50 and measured over any 250 consecutive TX UIs. (Also see the transmitter compliance eye diagram shown in Figure 48.)
3. A $T_{TX\text{-}EYE}$ = 0.70 UI provides for a total sum of deterministic and random jitter budget of $T_{TX\text{-}JITTER\text{-}MAX}$ = 0.30 UI for the transmitter collected over any 250 consecutive TX UIs. The $T_{TX\text{-}EYE\text{-}MEDIAN\text{-}to\text{-}MAX\text{-}JITTER}$ median is less than half of the total TX jitter budget collected over any 250 consecutive TX UIs. Note that the median is not the same as the mean. The jitter median describes the point in time where the number of jitter points on either side is approximately equal as opposed to the averaged time value.
4. The transmitter input impedance shall result in a differential return loss greater than or equal to 12 dB and a common mode return loss greater than or equal to 6 dB over a frequency range of 50 MHz to 1.25 GHz. This input impedance requirement applies to all valid input levels. The reference impedance for return loss measurements is 50 Ω to ground for both the D+ and D– line (that is, as measured by a vector network analyzer with 50-Ω probes—see Figure 50). Note that the series capacitors C_{TX} is optional for the return loss measurement.
5. Measured between 20%–80% at transmitter package pins into a test load as shown in Figure 50 for both $V_{TX\text{-}D+}$ and $V_{TX\text{-}D-}$.
6. See Section 4.3.1.8 of the *PCI Express Base Specifications Rev 1.0a.*
7. See Section 4.2.6.3 of the *PCI Express Base Specifications Rev 1.0a.*
8. MPC8548E SerDes transmitter does not have CTX built in. An external AC coupling capacitor is required.

17.4.2 Transmitter Compliance Eye Diagrams

The TX eye diagram in Figure 48 is specified using the passive compliance/test measurement load (see Figure 50) in place of any real PCI Express interconnect +RX component.

There are two eye diagrams that must be met for the transmitter. Both eye diagrams must be aligned in time using the jitter median to locate the center of the eye diagram. The different eye diagrams differ in voltage depending whether it is a transition bit or a de-emphasized bit. The exact reduced voltage level of the de-emphasized bit is always relative to the transition bit.

The eye diagram must be valid for any 250 consecutive UIs.

A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. The eye diagram is created using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI.

NOTE

It is recommended that the recovered TX UI is calculated using all edges in the 3500 consecutive UI interval with a fit algorithm using a minimization merit function (for example, least squares and median deviation fits).

Table 71. MPC8548E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
LSYNC_IN	F27	I	BV_{DD}	—
LSYNC_OUT	F28	O	BV_{DD}	—
DMA				
$\overline{\text{DMA\_DACK}}$[0:1]	AD3, AE1	O	OV_{DD}	5, 9, 102
$\overline{\text{DMA\_DREQ}}$[0:1]	AD4, AE2	I	OV_{DD}	—
$\overline{\text{DMA\_DDONE}}$[0:1]	AD2, AD1	O	OV_{DD}	—
Programmable Interrupt Controller				
$\overline{\text{UDE}}$	AH16	I	OV_{DD}	—
$\overline{\text{MCP}}$	AG19	I	OV_{DD}	—
IRQ[0:7]	AG23, AF18, AE18, AF20, AG18, AF17, AH24, AE20	I	OV_{DD}	—
IRQ[8]	AF19	I	OV_{DD}	—
IRQ[9]/$\overline{\text{DMA\_DREQ3}}$	AF21	I	OV_{DD}	1
IRQ[10]/$\overline{\text{DMA\_DACK3}}$	AE19	I/O	OV_{DD}	1
IRQ[11]/$\overline{\text{DMA\_DDONE3}}$	AD20	I/O	OV_{DD}	1
$\overline{\text{IRQ\_OUT}}$	AD18	O	OV_{DD}	2, 4
Ethernet Management Interface				
EC_MDC	AB9	O	OV_{DD}	5, 9
EC_MDIO	AC8	I/O	OV_{DD}	—
Gigabit Reference Clock				
EC_GTX_CLK125	V11	I	LV_{DD}	—
Three-Speed Ethernet Controller (Gigabit Ethernet 1)				
TSEC1_RXD[7:0]	R5, U1, R3, U2, V3, V1, T3, T2	I	LV_{DD}	—
TSEC1_TXD[7:0]	T10, V7, U10, U5, U4, V6, T5, T8	O	LV_{DD}	5, 9
TSEC1_COL	R4	I	LV_{DD}	—
TSEC1_CRS	V5	I/O	LV_{DD}	20
TSEC1_GTX_CLK	U7	O	LV_{DD}	—
TSEC1_RX_CLK	U3	I	LV_{DD}	—
TSEC1_RX_DV	V2	I	LV_{DD}	—
TSEC1_RX_ER	T1	I	LV_{DD}	—
TSEC1_TX_CLK	T6	I	LV_{DD}	—
TSEC1_TX_EN	U9	O	LV_{DD}	30
TSEC1_TX_ER	T7	O	LV_{DD}	—

Table 71. MPC8548E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
Clock				
RTC	AF16	I	OV_{DD}	—
SYSCLK	AH17	I	OV_{DD}	—
JTAG				
TCK	AG28	I	OV_{DD}	—
TDI	AH28	I	OV_{DD}	12
TDO	AF28	O	OV_{DD}	—
TMS	AH27	I	OV_{DD}	12
$\overline{\text{TRST}}$	AH23	I	OV_{DD}	12
DFT				
L1_TSTCLK	AC25	I	OV_{DD}	25
L2_TSTCLK	AE22	I	OV_{DD}	25
$\overline{\text{LSSD\_MODE}}$	AH20	I	OV_{DD}	25
$\overline{\text{TEST\_SEL}}$	AH14	I	OV_{DD}	25
Thermal Management				
THERM0	AG1	—	—	14
THERM1	AH1	—	—	14
Power Management				
ASLEEP	AH18	O	OV_{DD}	9, 19, 29
Power and Ground Signals				
GND	A11, B7, B24, C1, C3, C5, C12, C15, C26, D8, D11, D16, D20, D22, E1, E5, E9, E12, E15, E17, F4, F26, G12, G15, G18, G21, G24, H2, H6, H8, H28, J4, J12, J15, J17, J27, K7, K9, K11, K27, L3, L5, L12, L16, N11, N13, N15, N17, N19, P4, P9, P12, P14, P16, P18, R11, R13, R15, R17, R19, T4, T12, T14, T16, T18, U8, U11, U13, U15, U17, U19, V4, V12, V18, W6, W19, Y4, Y9, Y11, Y19, AA6, AA14, AA17, AA22, AA23, AB4, AC2, AC11, AC19, AC26, AD5, AD9, AD22, AE3, AE14, AF6, AF10, AF13, AG8, AG27, K28, L24, L26, N24, N27, P25, R28, T24, T26, U24, V25, W28, Y24, Y26, AA24, AA27, AB25, AC28, L21, L23, N22, P20, R23, T21, U22, V20, W23, Y21, U27	—	—	—
OV_{DD}	V16, W11, W14, Y18, AA13, AA21, AB11, AB17, AB24, AC4, AC9, AC21, AD6, AD13, AD17, AD19, AE10, AE8, AE24, AF4, AF12, AF22, AF27, AG26	Power for PCI and other standards (3.3 V)	OV_{DD}	—

Table 71. MPC8548E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
LV_{DD}	N8, R7, T9, U6	Power for TSEC1 and TSEC2 (2.5 V, 3.3 V)	LV_{DD}	—
TV_{DD}	W9, Y6	Power for TSEC3 and TSEC4 (2,5 V, 3.3 V)	TV_{DD}	—
GV_{DD}	B3, B11, C7, C9, C14, C17, D4, D6, D10, D15, E2, E8, E11, E18, F5, F12, F16, G3, G7, G9, G11, H5, H12, H15, H17, J10, K3, K12, K16, K18, L6, M4, M8, M13	Power for DDR1 and DDR2 DRAM I/O voltage (1.8 V, 2.5)	GV_{DD}	—
BV_{DD}	C21, C24, C27, E20, E25, G19, G23, H26, J20	Power for local bus (1.8 V, 2.5 V, 3.3 V)	BV_{DD}	—
V_{DD}	M19, N12, N14, N16, N18, P11, P13, P15, P17, P19, R12, R14, R16, R18, T11, T13, T15, T17, T19, U12, U14, U16, U18, V17, V19	Power for core (1.1 V)	V_{DD}	—
SV_{DD}	L25, L27, M24, N28, P24, P26, R24, R27, T25, V24, V26, W24, W27, Y25, AA28, AC27	Core Power for SerDes transceivers (1.1 V)	SV_{DD}	—
XV_{DD}	L20, L22, N23, P21, R22, T20, U23, V21, W22, Y20	Pad Power for SerDes transceivers (1.1 V)	XV_{DD}	—
AVDD_LBIU	J28	Power for local bus PLL (1.1 V)	—	26
AVDD_PCI1	AH21	Power for PCI1 PLL (1.1 V)	—	26
AVDD_PCI2	AH22	Power for PCI2 PLL (1.1 V)	—	26
AVDD_CORE	AH15	Power for e500 PLL (1.1 V)	—	26
AVDD_PLAT	AH19	Power for CCB PLL (1.1 V)	—	26
AVDD_SRDS	U25	Power for SRDSPLL (1.1 V)	—	26
SENSEVDD	M14	O	V_{DD}	13

Table 72. MPC8547E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
Reserved	U20, V22, W20, Y22	—	—	15
Reserved	U21, V23, W21, Y23	—	—	15
SD_PLL_TPD	U28	O	XV_{DD}	24
SD_REF_CLK	T28	I	XV_{DD}	—
$\overline{\text{SD\_REF\_CLK}}$	T27	I	XV_{DD}	—
Reserved	AC1, AC3	—	—	2
Reserved	M26, V28	—	—	32
Reserved	M25, V27	—	—	34
Reserved	M20, M21, T22, T23	—	—	38
General-Purpose Output				
GPOUT[24:31]	K26, K25, H27, G28, H25, J26, K24, K23	O	BV_{DD}	—
System Control				
$\overline{\text{HRESET}}$	AG17	I	OV_{DD}	—
$\overline{\text{HRESET\_REQ}}$	AG16	O	OV_{DD}	29
$\overline{\text{SRESET}}$	AG20	I	OV_{DD}	—
$\overline{\text{CKSTP\_IN}}$	AA9	I	OV_{DD}	—
$\overline{\text{CKSTP\_OUT}}$	AA8	O	OV_{DD}	2, 4
Debug				
TRIG_IN	AB2	I	OV_{DD}	—
TRIG_OUT/READY/$\overline{\text{QUIESCE}}$	AB1	O	OV_{DD}	6, 9, 19, 29
MSRCID[0:1]	AE4, AG2	O	OV_{DD}	5, 6, 9
MSRCID[2:4]	AF3, AF1, AF2	O	OV_{DD}	6, 19, 29
MDVAL	AE5	O	OV_{DD}	6
CLK_OUT	AE21	O	OV_{DD}	11
Clock				
RTC	AF16	I	OV_{DD}	—
SYSCLK	AH17	I	OV_{DD}	—
JTAG				
TCK	AG28	I	OV_{DD}	—
TDI	AH28	I	OV_{DD}	12
TDO	AF28	O	OV_{DD}	—
TMS	AH27	I	OV_{DD}	12
$\overline{\text{TRST}}$	AH23	I	OV_{DD}	12

Table 73. MPC8545E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
FIFO1_RXC2	P5	I	LV_{DD}	104
Reserved	R1	—	—	104
Reserved	P10	—	—	105
FIFO1_TXC2	P7	O	LV_{DD}	15
cfg_dram_type1	R10	I	LV_{DD}	5
Three-Speed Ethernet Controller (Gigabit Ethernet 3)				
TSEC3_TXD[3:0]	V8, W10, Y10, W7	O	TV_{DD}	5, 9, 29
TSEC3_RXD[3:0]	Y1, W3, W5, W4	I	TV_{DD}	—
TSEC3_GTX_CLK	W8	O	TV_{DD}	—
TSEC3_RX_CLK	W2	I	TV_{DD}	—
TSEC3_RX_DV	W1	I	TV_{DD}	—
TSEC3_RX_ER	Y2	I	TV_{DD}	—
TSEC3_TX_CLK	V10	I	TV_{DD}	—
TSEC3_TX_EN	V9	O	TV_{DD}	30
TSEC3_TXD[7:4]	AB8, Y7, AA7, Y8	O	TV_{DD}	5, 9, 29
TSEC3_RXD[7:4]	AA1, Y3, AA2, AA4	I	TV_{DD}	—
Reserved	AA5	—	—	15
TSEC3_COL	Y5	I	TV_{DD}	—
TSEC3_CRS	AA3	I/O	TV_{DD}	31
TSEC3_TX_ER	AB6	O	TV_{DD}	—
DUART				
$\overline{\text{UART\_CTS}}$[0:1]	AB3, AC5	I	OV_{DD}	—
$\overline{\text{UART\_RTS}}$[0:1]	AC6, AD7	O	OV_{DD}	—
UART_SIN[0:1]	AB5, AC7	I	OV_{DD}	—
UART_SOUT[0:1]	AB7, AD8	O	OV_{DD}	—
I^2C interface				
IIC1_SCL	AG22	I/O	OV_{DD}	4, 27
IIC1_SDA	AG21	I/O	OV_{DD}	4, 27
IIC2_SCL	AG15	I/O	OV_{DD}	4, 27
IIC2_SDA	AG14	I/O	OV_{DD}	4, 27
SerDes				
SD_RX[0:3]	M28, N26, P28, R26	I	XV_{DD}	—
$\overline{\text{SD\_RX}}$[0:3]	M27, N25, P27, R25	I	XV_{DD}	—
SD_TX[0:3]	M22, N20, P22, R20	O	XV_{DD}	—

Table 73. MPC8545E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
TDO	AF28	O	OV_{DD}	—
TMS	AH27	I	OV_{DD}	12
$\overline{\text{TRST}}$	AH23	I	OV_{DD}	12
DFT				
L1_TSTCLK	AC25	I	OV_{DD}	25
L2_TSTCLK	AE22	I	OV_{DD}	25
$\overline{\text{LSSD\_MODE}}$	AH20	I	OV_{DD}	25
$\overline{\text{TEST\_SEL}}$	AH14	I	OV_{DD}	25
Thermal Management				
THERM0	AG1	—	—	14
THERM1	AH1	—	—	14
Power Management				
ASLEEP	AH18	O	OV_{DD}	9, 19, 29
Power and Ground Signals				
GND	A11, B7, B24, C1, C3, C5, C12, C15, C26, D8, D11, D16, D20, D22, E1, E5, E9, E12, E15, E17, F4, F26, G12, G15, G18, G21, G24, H2, H6, H8, H28, J4, J12, J15, J17, J27, K7, K9, K11, K27, L3, L5, L12, L16, N11, N13, N15, N17, N19, P4, P9, P12, P14, P16, P18, R11, R13, R15, R17, R19, T4, T12, T14, T16, T18, U8, U11, U13, U15, U17, U19, V4, V12, V18, W6, W19, Y4, Y9, Y11, Y19, AA6, AA14, AA17, AA22, AA23, AB4, AC2, AC11, AC19, AC26, AD5, AD9, AD22, AE3, AE14, AF6, AF10, AF13, AG8, AG27, K28, L24, L26, N24, N27, P25, R28, T24, T26, U24, V25, W28, Y24, Y26, AA24, AA27, AB25, AC28, L21, L23, N22, P20, R23, T21, U22, V20, W23, Y21, U27	—	—	—
OV_{DD}	V16, W11, W14, Y18, AA13, AA21, AB11, AB17, AB24, AC4, AC9, AC21, AD6, AD13, AD17, AD19, AE10, AE8, AE24, AF4, AF12, AF22, AF27, AG26	Power for PCI and other standards (3.3 V)	OV_{DD}	—
LV_{DD}	N8, R7, T9, U6	Power for TSEC1 and TSEC2 (2.5 V, 3.3 V)	LV_{DD}	—
TV_{DD}	W9, Y6	Power for TSEC3 and TSEC4 (2,5 V, 3.3 V)	TV_{DD}	—

Table 74. MPC8543E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
LSYNC_IN	F27	I	BV_{DD}	—
LSYNC_OUT	F28	O	BV_{DD}	—
DMA				
$\overline{\text{DMA\_DACK}}$[0:1]	AD3, AE1	O	OV_{DD}	5, 9, 108
$\overline{\text{DMA\_DREQ}}$[0:1]	AD4, AE2	I	OV_{DD}	—
$\overline{\text{DMA\_DDONE}}$[0:1]	AD2, AD1	O	OV_{DD}	—
Programmable Interrupt Controller				
$\overline{\text{UDE}}$	AH16	I	OV_{DD}	—
$\overline{\text{MCP}}$	AG19	I	OV_{DD}	—
IRQ[0:7]	AG23, AF18, AE18, AF20, AG18, AF17, AH24, AE20	I	OV_{DD}	—
IRQ[8]	AF19	I	OV_{DD}	—
IRQ[9]/$\overline{\text{DMA\_DREQ3}}$	AF21	I	OV_{DD}	1
IRQ[10]/$\overline{\text{DMA\_DACK3}}$	AE19	I/O	OV_{DD}	1
IRQ[11]/$\overline{\text{DMA\_DDONE3}}$	AD20	I/O	OV_{DD}	1
$\overline{\text{IRQ\_OUT}}$	AD18	O	OV_{DD}	2, 4
Ethernet Management Interface				
EC_MDC	AB9	O	OV_{DD}	5, 9
EC_MDIO	AC8	I/O	OV_{DD}	—
Gigabit Reference Clock				
EC_GTX_CLK125	V11	I	LV_{DD}	—
Three-Speed Ethernet Controller (Gigabit Ethernet 1)				
TSEC1_RXD[7:0]	R5, U1, R3, U2, V3, V1, T3, T2	I	LV_{DD}	—
TSEC1_TXD[7:0]	T10, V7, U10, U5, U4, V6, T5, T8	O	LV_{DD}	5, 9
TSEC1_COL	R4	I	LV_{DD}	—
TSEC1_CRS	V5	I/O	LV_{DD}	20
TSEC1_GTX_CLK	U7	O	LV_{DD}	—
TSEC1_RX_CLK	U3	I	LV_{DD}	—
TSEC1_RX_DV	V2	I	LV_{DD}	—
TSEC1_RX_ER	T1	I	LV_{DD}	—
TSEC1_TX_CLK	T6	I	LV_{DD}	—
TSEC1_TX_EN	U9	O	LV_{DD}	30
TSEC1_TX_ER	T7	O	LV_{DD}	—
GPIN[0:7]	P2, R2, N1, N2, P3, M2, M1, N3	I	LV_{DD}	103

Table 74. MPC8543E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
IIC1_SDA	AG21	I/O	OV_{DD}	4, 27
IIC2_SCL	AG15	I/O	OV_{DD}	4, 27
IIC2_SDA	AG14	I/O	OV_{DD}	4, 27
SerDes				
SD_RX[0:7]	M28, N26, P28, R26, W26, Y28, AA26, AB28	I	XV_{DD}	—
$\overline{\text{SD\_RX}}$[0:7]	M27, N25, P27, R25, W25, Y27, AA25, AB27	I	XV_{DD}	—
SD_TX[0:7]	M22, N20, P22, R20, U20, V22, W20, Y22	O	XV_{DD}	—
$\overline{\text{SD\_TX}}$[0:7]	M23, N21, P23, R21, U21, V23, W21, Y23	O	XV_{DD}	—
SD_PLL_TPD	U28	O	XV_{DD}	24
SD_REF_CLK	T28	I	XV_{DD}	—
$\overline{\text{SD\_REF\_CLK}}$	T27	I	XV_{DD}	—
Reserved	AC1, AC3	—	—	2
Reserved	M26, V28	—	—	32
Reserved	M25, V27	—	—	34
Reserved	M20, M21, T22, T23	—	—	38
General-Purpose Output				
GPOUT[24:31]	K26, K25, H27, G28, H25, J26, K24, K23	O	BV_{DD}	—
System Control				
$\overline{\text{HRESET}}$	AG17	I	OV_{DD}	—
$\overline{\text{HRESET\_REQ}}$	AG16	O	OV_{DD}	29
$\overline{\text{SRESET}}$	AG20	I	OV_{DD}	—
$\overline{\text{CKSTP\_IN}}$	AA9	I	OV_{DD}	—
$\overline{\text{CKSTP\_OUT}}$	AA8	O	OV_{DD}	2, 4
Debug				
TRIG_IN	AB2	I	OV_{DD}	—
TRIG_OUT/READY/$\overline{\text{QUIESCE}}$	AB1	O	OV_{DD}	6, 9, 19, 29
MSRCID[0:1]	AE4, AG2	O	OV_{DD}	5, 6, 9
MSRCID[2:4]	AF3, AF1, AF2	O	OV_{DD}	6, 19, 29
MDVAL	AE5	O	OV_{DD}	6
CLK_OUT	AE21	O	OV_{DD}	11
Clock				
RTC	AF16	I	OV_{DD}	—
SYSCLK	AH17	I	OV_{DD}	—

21 Thermal

This section describes the thermal specifications of the device.

21.1 Thermal for Version 2.0 Silicon HiCTE FC-CBGA with Full Lid

This section describes the thermal specifications for the HiCTE FC-CBGA package for revision 2.0 silicon.

This table shows the package thermal characteristics.

Table 84. Package Thermal Characteristics for HiCTE FC-CBGA

Characteristic	JEDEC Board	Symbol	Value	Unit	Notes
Die junction-to-ambient (natural convection)	Single-layer board (1s)	$R_{\theta JA}$	17	°C/W	1, 2
Die junction-to-ambient (natural convection)	Four-layer board (2s2p)	$R_{\theta JA}$	12	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Single-layer board (1s)	$R_{\theta JA}$	11	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Four-layer board (2s2p)	$R_{\theta JA}$	8	°C/W	1, 2
Die junction-to-board	N/A	$R_{\theta JB}$	3	°C/W	3
Die junction-to-case	N/A	$R_{\theta JC}$	0.8	°C/W	4

Notes:

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, airflow, power dissipation of other components on the board, and board thermal resistance.
2. Per JEDEC JESD51-6 with the board (JESD51-7) horizontal.
3. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
4. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1). The cold plate temperature is used for the case temperature, measured value includes the thermal resistance of the interface layer.

21.2 Thermal for Version 2.1.1, 2.1.2, and 2.1.3 Silicon FC-PBGA with Full Lid and Version 3.1.x Silicon with Stamped Lid

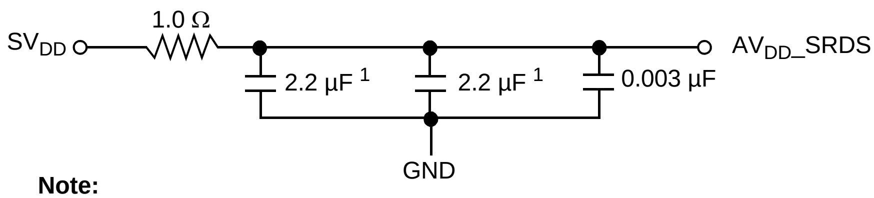
This section describes the thermal specifications for the FC-PBGA package for revision 2.1.1, 2.1.2, and 3.0 silicon.

This table shows the package thermal characteristics.

Table 85. Package Thermal Characteristics for FC-PBGA

Characteristic	JEDEC Board	Symbol	Value	Unit	Notes
Die junction-to-ambient (natural convection)	Single-layer board (1s)	$R_{\theta JA}$	18	°C/W	1, 2
Die junction-to-ambient (natural convection)	Four-layer board (2s2p)	$R_{\theta JA}$	13	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Single-layer board (1s)	$R_{\theta JA}$	13	°C/W	1, 2
Die junction-to-ambient (200 ft/min)	Four-layer board (2s2p)	$R_{\theta JA}$	9	°C/W	1, 2

the ground plane. Use ceramic chip capacitors with the highest possible self-resonant frequency. All traces must be kept short, wide and direct.



Note:
1. An 0805 sized capacitor is recommended for system initial bring-up.

Figure 60. SerDes PLL Power Supply Filter

Note the following:

- AV_{DD}_SRDS must be a filtered version of SV_{DD}.
- Signals on the SerDes interface are fed from the XV_{DD} power plane.

22.3 Decoupling Recommendations

Due to large address and data buses, and high operating frequencies, the device can generate transient power surges and high frequency noise in its power supply, especially while driving large capacitive loads. This noise must be prevented from reaching other components in the device system, and the device itself requires a clean, tightly regulated source of power. Therefore, it is recommended that the system designer place at least one decoupling capacitor at each V_{DD}, TV_{DD}, BV_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} pin of the device. These decoupling capacitors must receive their power from separate V_{DD}, TV_{DD}, BV_{DD}, OV_{DD}, GV_{DD}, LV_{DD}, and GND power planes in the PCB, utilizing short low impedance traces to minimize inductance. Capacitors must be placed directly under the device using a standard escape pattern as much as possible. If some caps are to be placed surrounding the part it must be routed with large trace to minimize the inductance.

These capacitors must have a value of 0.1 µF. Only ceramic SMT (surface mount technology) capacitors must be used to minimize lead inductance, preferably 0402 or 0603 sizes. Besides, it is recommended that there be several bulk storage capacitors distributed around the PCB, feeding the V_{DD}, TV_{DD}, BV_{DD}, OV_{DD}, GV_{DD}, and LV_{DD}, planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors must have a low ESR (equivalent series resistance) rating to ensure the quick response time necessary. They must also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors—100–330 µF (AVX TPS tantalum or Sanyo OSCON). However, customers must work directly with their power regulator vendor for best values, types and quantity of bulk capacitors.

22.4 SerDes Block Power Supply Decoupling Recommendations

The SerDes block requires a clean, tightly regulated source of power (SV_{DD} and XV_{DD}) to ensure low jitter on transmit and reliable recovery of data in the receiver. An appropriate decoupling scheme is outlined below.

Only surface mount technology (SMT) capacitors must be used to minimize inductance. Connections from all capacitors to power and ground must be done with multiple vias to further reduce inductance.

- First, the board must have at least 10 × 10-nF SMT ceramic chip capacitors as close as possible to the supply balls of the device. Where the board has blind vias, these capacitors must be placed directly below the chip supply and ground connections. Where the board does not have blind vias, these capacitors must be placed in a ring around the device as close to the supply and ground connections as possible.
- Second, there must be a 1-µF ceramic chip capacitor from each SerDes supply (SV_{DD} and XV_{DD}) to the board ground plane on each side of the device. This must be done for all SerDes supplies.
- Third, between the device and any SerDes voltage regulator there must be a 10-µF, low equivalent series resistance (ESR) SMT tantalum chip capacitor and a 100-µF, low ESR SMT tantalum chip capacitor. This must be done for all SerDes supplies.

22.5 Connection Recommendations

To ensure reliable operation, it is highly recommended to connect unused inputs to an appropriate signal level. All unused active low inputs must be tied to V_{DD}, TV_{DD}, BV_{DD}, OV_{DD}, GV_{DD}, and LV_{DD}, as required. All unused active high inputs must be connected to GND. All NC (no-connect) signals must remain unconnected. Power and ground connections must be made to all external V_{DD}, TV_{DD}, BV_{DD}, OV_{DD}, GV_{DD}, LV_{DD}, and GND pins of the device.

22.6 Pull-Up and Pull-Down Resistor Requirements

The device requires weak pull-up resistors (2–10 kΩ is recommended) on open drain type pins including I^{2}C pins and PIC (interrupt) pins.

Correct operation of the JTAG interface requires configuration of a group of system control pins as demonstrated in Figure 63. Care must be taken to ensure that these pins are maintained at a valid deasserted state under normal operating conditions as most have asynchronous behavior and spurious assertion gives unpredictable results.

The following pins must not be pulled down during power-on reset: TSEC3_TXD[3], $\overline{\text{HRESET\_REQ}}$, TRIG_OUT/READY/$\overline{\text{QUIESCE}}$, MSRCID[2:4], ASLEEP. The $\overline{\text{DMA\_DACK}}$[0:1], and TEST_SEL/$\overline{\text{TEST\_SEL}}$ pins must be set to a proper state during POR configuration. See the pinlist table of the individual device for more details

See the PCI 2.2 specification for all pull ups required for PCI.

22.7 Output Buffer DC Impedance

The device drivers are characterized over process, voltage, and temperature. For all buses, the driver is a push-pull single-ended driver type (open drain for I^{2}C).

To measure Z_0 for the single-ended drivers, an external resistor is connected from the chip pad to OV_{DD} or GND. Then, the value of each resistor is varied until the pad voltage is $OV_{DD}/2$ (see Figure 61). The output impedance is the average of two components, the resistances of the pull-up and pull-down devices. When data is held high, SW1 is closed (SW2 is open) and R_P is trimmed until the voltage at the pad equals $OV_{DD}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N)/2$.

23 Ordering Information

Ordering information for the parts fully covered by this specification document is provided in Section 23.1, “Part Numbers Fully Addressed by this Document.”

23.1 Part Numbers Fully Addressed by this Document

This table provides the Freescale part numbering nomenclature for the device. Note that the individual part numbers correspond to a maximum processor core frequency. For available frequencies, contact your local Freescale sales office. In addition to the processor frequency, the part-numbering scheme also includes an application modifier that may specify special application conditions. Each part number also contains a revision code that refers to the die mask revision number.

Table 87. Part Numbering Nomenclature

MPC	*nnnnn*	*t*	*pp*	*ff*	*c*	*r*
Product Code	**Part Identifier**	**Temperature**	**Package[1, 2, 3]**	**Processor Frequency[4]**	**Core Frequency**	**Silicon Version**
MPC	8548E	Blank = 0 to 105°C C = –40° to 105°C	HX = CBGA VU = Pb-free CBGA PX = PBGA VT = Pb-free PBGA	AV = 1500[3] AU = 1333 AT = 1200 AQ = 1000	J = 533 H = 500[5] G = 400	Blank = Ver. 2.0 (SVR = 0x80390020) A = Ver. 2.1.1 B = Ver. 2.1.2 C = Ver. 2.1.3 (SVR = 0x80390021) D = Ver. 3.1.x (SVR = 0x80390031)
	8548					Blank = Ver. 2.0 (SVR = 0x80310020) A = Ver. 2.1.1 B = Ver. 2.1.2 C = Ver. 2.1.3 (SVR = 0x80310021) D = Ver. 3.1.x (SVR = 0x80310031)
	8547E			AU = 1333 AT = 1200 AQ = 1000	J = 533 G = 400	Blank = Ver. 2.0 (SVR = 0x80390120) A = Ver. 2.1.1 B = Ver. 2.1.2 C = Ver. 2.1.3 (SVR = 0x80390121) D = Ver. 3.1.x (SVR = 0x80390131)
	8547					Blank = Ver. 2.0 (SVR = 0x80390120) A = Ver. 2.1.1 B = Ver. 2.1.2 C = Ver. 2.1.3 (SVR = 0x80310121) D = Ver. 3.1.x (SVR = 0x80310131)